

APT2X31D60J      600V      30A  
APT2X30D60J      600V      30A

## DUAL DIE ISOTOP® PACKAGE

## ULTRAFAST SOFT RECOVERY RECTIFIER DIODE

### PRODUCT APPLICATIONS

- Anti-Parallel Diode
  - Switchmode Power Supply
  - Inverters
- Free Wheeling Diode
  - Motor Controllers
  - Converters
- Snubber Diode
- Uninterruptible Power Supply (UPS)
- Induction Heating
- High Speed Rectifiers

### PRODUCT FEATURES

- Ultrafast Recovery Times
- Soft Recovery Characteristics
- Popular SOT-227 Package
- Low Forward Voltage
- High Blocking Voltage
- Low Leakage Current

### PRODUCT BENEFITS

- Low Losses
- Low Noise Switching
- Cooler Operation
- Higher Reliability Systems
- Increased System Power Density

### MAXIMUM RATINGS

All Ratings:  $T_C = 25^\circ\text{C}$  unless otherwise specified.

Symbol	Characteristic / Test Conditions	APT2X31_31D60J	UNIT
$V_R$	Maximum D.C. Reverse Voltage	600	Volts
$V_{RRM}$	Maximum Peak Repetitive Reverse Voltage		
$V_{RWM}$	Maximum Working Peak Reverse Voltage		
$I_{F(AV)}$	Maximum Average Forward Current ( $T_C = 112^\circ\text{C}$ , Duty Cycle = 0.5)	30	Amps
$I_{F(RMS)}$	RMS Forward Current (Square wave, 50% duty)	49	
$I_{FSM}$	Non-Repetitive Forward Surge Current ( $T_J = 45^\circ\text{C}$ , 8.3ms)	320	
$T_J, T_{STG}$	Operating and Storage Temperature Range	-55 to 175	$^\circ\text{C}$
$T_L$	Lead Temperature for 10 Sec.	300	

### STATIC ELECTRICAL CHARACTERISTICS

Symbol	Characteristic / Test Conditions	MIN	TYP	MAX	UNIT	
$V_F$	Forward Voltage		$I_F = 30\text{A}$	1.6	1.8	Volts
			$I_F = 60\text{A}$	1.9		
			$I_F = 30\text{A}, T_J = 125^\circ\text{C}$	1.4		
$I_{RM}$	Maximum Reverse Leakage Current		$V_R = V_R$ Rated		250	$\mu\text{A}$
			$V_R = V_R$ Rated, $T_J = 125^\circ\text{C}$		500	
$C_T$	Junction Capacitance, $V_R = 200\text{V}$		44		pF	

# DYNAMIC CHARACTERISTICS

APT2X31\_30D60J

Symbol	Characteristic	Test Conditions	MIN	TYP	MAX	UNIT
$t_{rr}$	Reverse Recovery Time	$I_F = 1A, di_F/dt = -100A/\mu s, V_R = 30V, T_J = 25^\circ C$	-	23		ns
$t_{rr}$	Reverse Recovery Time	$I_F = 30A, di_F/dt = -200A/\mu s, V_R = 400V, T_C = 25^\circ C$	-	85		
$Q_{rr}$	Reverse Recovery Charge		-	130		nC
$I_{RRM}$	Maximum Reverse Recovery Current		-	4	-	Amps
$t_{rr}$	Reverse Recovery Time	$I_F = 30A, di_F/dt = -200A/\mu s, V_R = 400V, T_C = 125^\circ C$	-	160		ns
$Q_{rr}$	Reverse Recovery Charge		-	700		nC
$I_{RRM}$	Maximum Reverse Recovery Current		-	8	-	Amps
$t_{rr}$	Reverse Recovery Time	$I_F = 30A, di_F/dt = -1000A/\mu s, V_R = 400V, T_C = 125^\circ C$	-	70		ns
$Q_{rr}$	Reverse Recovery Charge		-	1300		nC
$I_{RRM}$	Maximum Reverse Recovery Current		-	30		Amps

# THERMAL AND MECHANICAL CHARACTERISTICS

Symbol	Characteristic / Test Conditions	MIN	TYP	MAX	UNIT
$R_{\theta JC}$	Junction-to-Case Thermal Resistance			1.2	$^\circ C/W$
$R_{\theta JA}$	Junction-to-Ambient Thermal Resistance			20	
$W_T$	Package Weight		1.03		oz
			29.2		g
Torque	Maximum Mounting Torque			10	lb•in
				1.1	N•m

APT Reserves the right to change, without notice, the specifications and information contained herein.

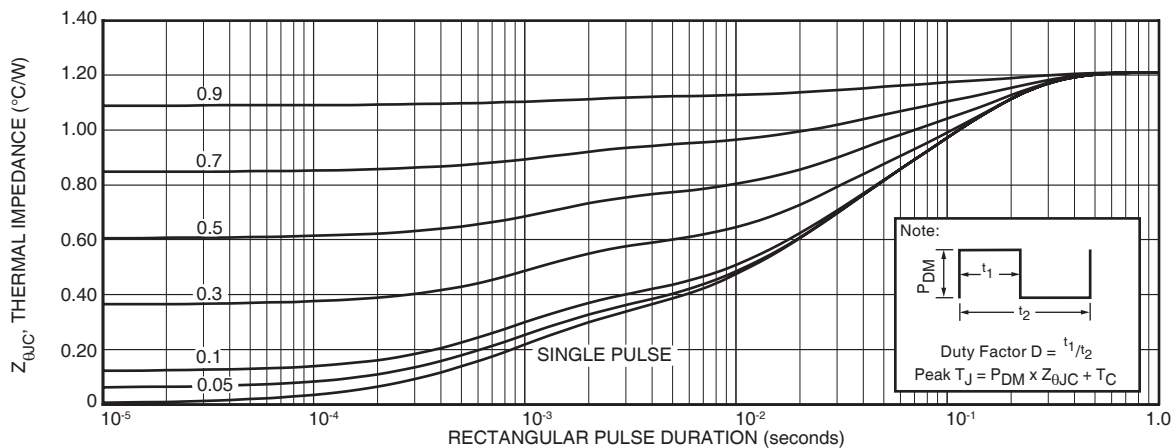


FIGURE 1a. MAXIMUM EFFECTIVE TRANSIENT THERMAL IMPEDANCE, JUNCTION-TO-CASE vs. PULSE DURATION

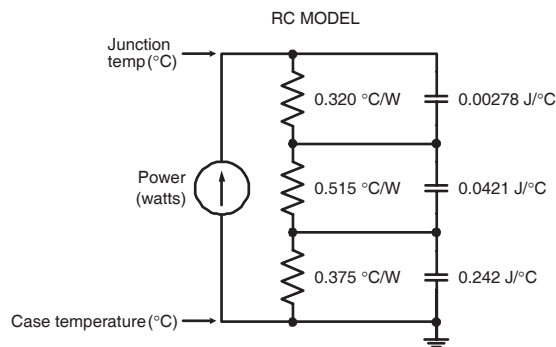


FIGURE 1b. TRANSIENT THERMAL IMPEDANCE MODEL

# TYPICAL PERFORMANCE CURVES

APT2X31\_30D60J

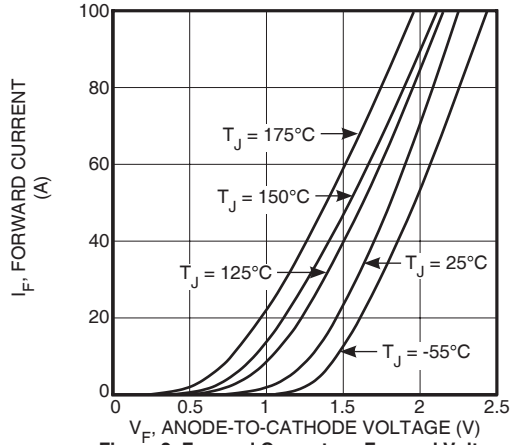


Figure 2. Forward Current vs. Forward Voltage

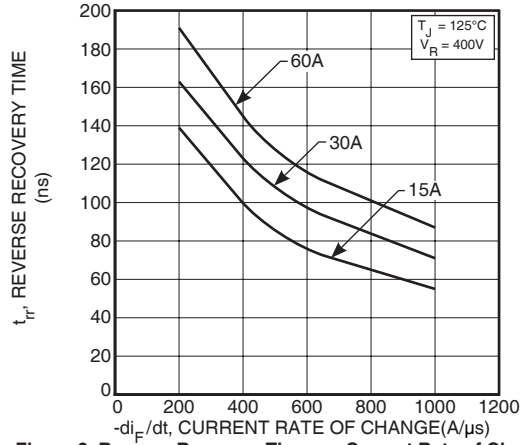


Figure 3. Reverse Recovery Time vs. Current Rate of Change

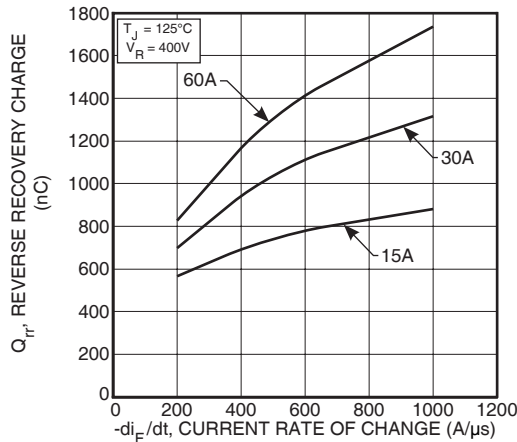


Figure 4. Reverse Recovery Charge vs. Current Rate of Change

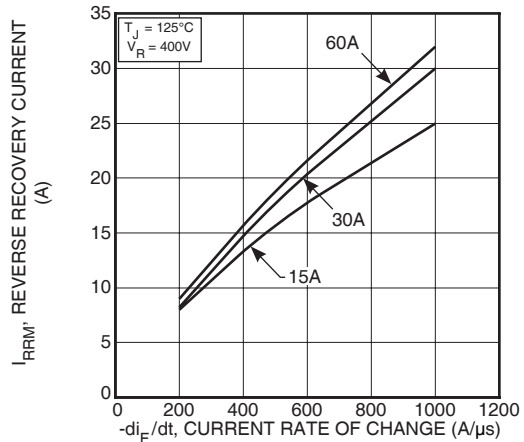


Figure 5. Reverse Recovery Current vs. Current Rate of Change

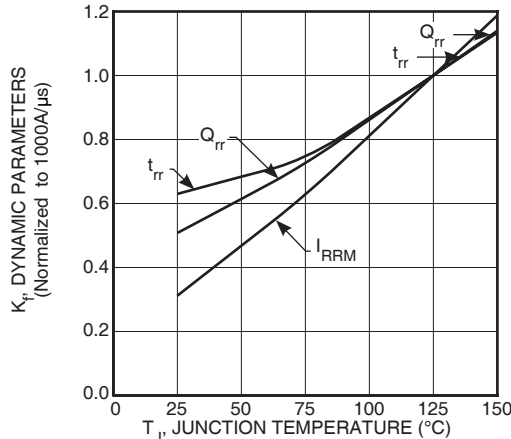


Figure 6. Dynamic Parameters vs. Junction Temperature

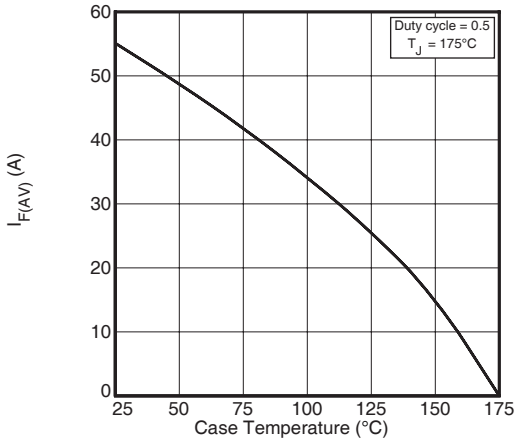


Figure 7. Maximum Average Forward Current vs. Case Temperature

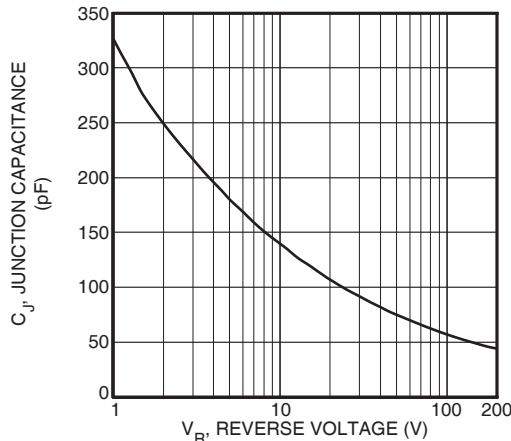


Figure 8. Junction Capacitance vs. Reverse Voltage

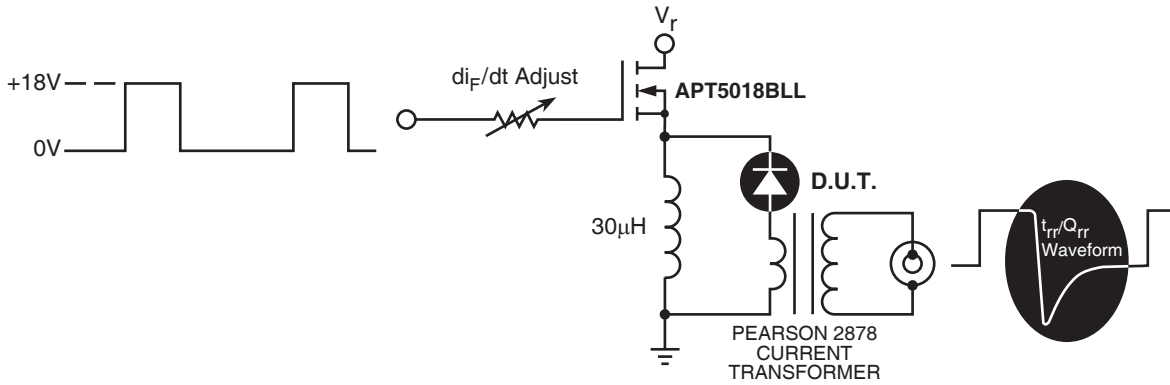


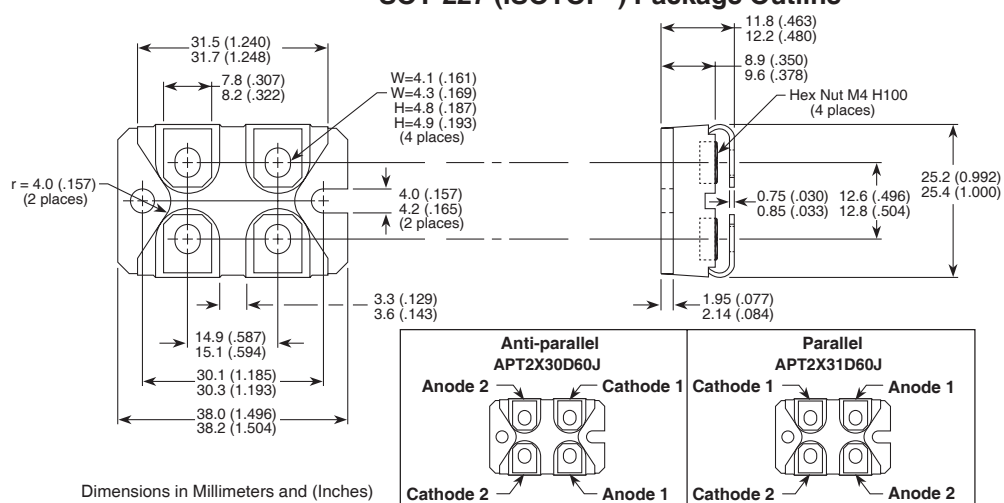
Figure 9. Diode Test Circuit

- 1  $I_F$  - Forward Conduction Current
- 2  $di_F/dt$  - Rate of Diode Current Change Through Zero Crossing.
- 3  $I_{RRM}$  - Maximum Reverse Recovery Current.
- 4  $t_{rr}$  - Reverse Recovery Time, measured from zero crossing where diode current goes from positive to negative, to the point at which the straight line through  $I_{RRM}$  and  $0.25 \cdot I_{RRM}$  passes through zero.
- 5  $Q_{rr}$  - Area Under the Curve Defined by  $I_{RRM}$  and  $t_{rr}$ .

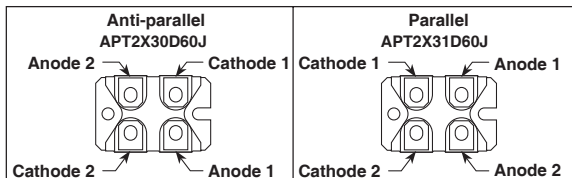


Figure 10, Diode Reverse Recovery Waveform and Definitions

SOT-227 (ISOTOP®) Package Outline



Dimensions in Millimeters and (Inches)



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